

In the Claims

Please amend the claims as follows:

Claims 1-43 (Cancelled)

44. (Currently Amended) A method of manufacturing an epitaxial silicon wafer substrate comprising:

Setting an upper limit that is defined by a straight line connecting a point at which a nitrogen concentration in a silicon ingot is 3×10^{15} atoms/cm³ when an oxygen concentration in the silicon ingot is 7×10^{17} atoms/cm³ and a point at which the nitrogen concentration is 3×10^{14} atoms/cm³ when the oxygen concentration is 1.6×10^{18} atoms/cm³ within a concentration range where the oxygen concentration and the nitrogen concentration are plotted along the horizontal axis and the vertical axis, and also setting a lower limit of the amount of added nitrogen, which is a function of an initial oxygen concentration of a silicon wafer substrate for ensuring a sufficient density of oxygen precipitates as gettering sites;

controlling ~~an~~ the oxygen concentration in accordance with a change in ~~a~~ the nitrogen concentration based on a characteristic that the nitrogen concentration increases from a shoulder portion to a tail portion of ~~a~~ the silicon ingot, so that the oxygen concentration and the nitrogen concentration fall within ~~a~~ the upper limit and the lower limit concentration range where ~~an upper limit is defined by a line connecting a point at which the nitrogen concentration is 3×10^{15} atoms/cm³ when the oxygen concentration is 7×10^{17} atoms/cm³ and a point at which the nitrogen concentration is 3×10^{14} atoms/cm³ when the oxygen concentration is 1.6×10^{18} atoms/cm³ within the concentration range where the oxygen~~

econcentration and the nitrogen concentration are plotted along the horizontal axis and the vertical axis at the same time when the silicon ingot is pulled up from a silicon raw material melt doped with nitrogen so that the nitrogen concentration at the tail portion of the silicon ingot is less than 3×10^{15} atoms/cm³;

Obtaining the silicon wafer substrate by slicing the pulled-up silicon ingot; and mirror polishing the obtained silicon wafer substrate; and then immediately after the step of mirror polishing, subjecting the obtained silicon wafer substrate to epitaxial growth processing.